

Title (en)

METHOD FOR THE MANUFACTURE OF A CAPACITOR AND CAPACITOR OBTAINED

Title (de)

VERFAHREN ZUR HERSTELLUNG EINES KONDENSATORS UND AUF DIESE WEISE HERGESTELLTER KONDENSATOR

Title (fr)

PROCEDE DE FABRICATION DE CONDENSATEUR ET CONDENSATEUR ISSU D'UN TEL PROCEDE

Publication

**EP 0731974 A1 19960918 (FR)**

Application

**EP 95902822 A 19941201**

Priority

- FR 9401404 W 19941201
- FR 9314519 A 19931203

Abstract (en)

[origin: WO9515570A1] Method for the manufacture of a stacked-type capacitor consisting of alternating dielectric layers and conducting layers. The dielectric and conducting layers are deposited in succession. The dielectric layers are deposited by polymerization of elements derived from the dissociation, by remote nitrogen plasma, of an organo-siliceous or organo-germanium gas. The conducting layers are formed by deposition of conducting elements derived from the dissociation, by remote nitrogen plasma, of a precursor gas of the conducting elements.

IPC 1-7

**H01G 4/30**; **H01G 4/008**; **H01G 4/012**

IPC 8 full level

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CPC (source: EP KR)

**H01F 38/28** (2013.01 - KR); **H01G 4/0085** (2013.01 - EP); **H01G 4/012** (2013.01 - EP); **H01G 4/30** (2013.01 - EP)

Citation (search report)

See references of WO 9515570A1

Designated contracting state (EPC)

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